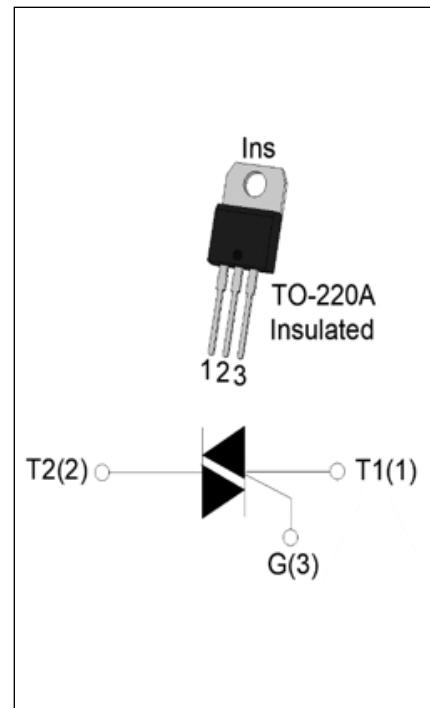


**DESCRIPTION:**

The JST139A-800D triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an internal ceramic pad, JST139A-800D provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

**MAIN FEATURES**

| Symbol                      | Value    | Unit |
|-----------------------------|----------|------|
| $I_{T(RMS)}$                | 16       | A    |
| $V_{DRM}/V_{RRM}$           | 800      | V    |
| $I_{GT\text{ I/II/III/IV}}$ | 5/5/5/10 | mA   |

**ABSOLUTE MAXIMUM RATINGS**

| Parameter   | Symbol           | Value    | Unit                   |
|---|------------------|----------|------------------------|
| Storage junction temperature range  | $T_{stg}$        | -40-150  | °C                     |
| Operating junction temperature range  | $T_j$            | -40-125  | °C                     |
| Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )  | $V_{DRM}$        | 800      | V                      |
| Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )  | $V_{RRM}$        | 800      | V                      |
| RMS on-state current ( $T_c \leq 72^\circ\text{C}$ )  | $I_{T(RMS)}$     | 16       | A                      |
| Non repetitive surge peak on-state current<br>(full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )            | $I_{TSM}$        | 140      | A                      |
| Non repetitive surge peak on-state current<br>(full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )          |                  | 154      |                        |
| $I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )  | $I^2t$           | 98       | $\text{A}^2\text{s}$   |
| Critical rate of rise of on-state current<br>( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ ) | I - II<br>III-IV | 50<br>20 | $\text{A}/\mu\text{s}$ |
| Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )   | $I_{GM}$         | 4        |                        |
| Average gate power dissipation ( $T_j=125^\circ\text{C}$ )  | $P_{G(AV)}$      | 0.5      | W                      |
| Peak gate power   | $P_{GM}$         | 10       | W                      |

|  |                 |     |    |
|--|-----------------|-----|----|
| Peak pulse voltage<br>(T <sub>j</sub> =25°C; non-repetitive,off-state;FIG.7) | V <sub>pp</sub> | 4.5 | kV |
|--|-----------------|-----|----|

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**

| Symbol           | Test Condition  | Quadrant    | Value |     | Unit |
|------------------|---|-------------|-------|-----|------|
| I <sub>GT</sub>  | V <sub>D</sub> =12V R <sub>L</sub> =33Ω   | I - II -III | MAX.  | 5   | mA   |
|                  |   | IV          |       | 10  |      |
| V <sub>GT</sub>  |   | ALL         | MAX.  | 1   | V    |
| V <sub>GD</sub>  | V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C<br>R <sub>L</sub> =3.3KΩ         | ALL         | MIN.  | 0.2 | V    |
| I <sub>L</sub>   | I <sub>G</sub> =1.2I <sub>GT</sub>  | I - III-IV  | MAX.  | 15  | mA   |
|                  |   | II          |       | 20  |      |
| I <sub>H</sub>   | I <sub>T</sub> =500mA   |             | MAX.  | 10  | mA   |
| dV/dt            | V <sub>D</sub> =540V Gate Open T <sub>j</sub> =125°C                                    |             | MIN.  | 40  | V/μs |
| (dV/dt)c         | (dI/dt)c=7.2A/ms, T <sub>j</sub> =110°C   |             | MIN.  | 2   | V/μs |
| t <sub>on</sub>  | I <sub>G</sub> =20mA I <sub>A</sub> =200mA I <sub>R</sub> =20mA<br>T <sub>j</sub> =25°C | TYP.        | 3     | μs  |      |
| t <sub>off</sub> |   |             | 50    |     |      |

**STATIC CHARACTERISTICS**

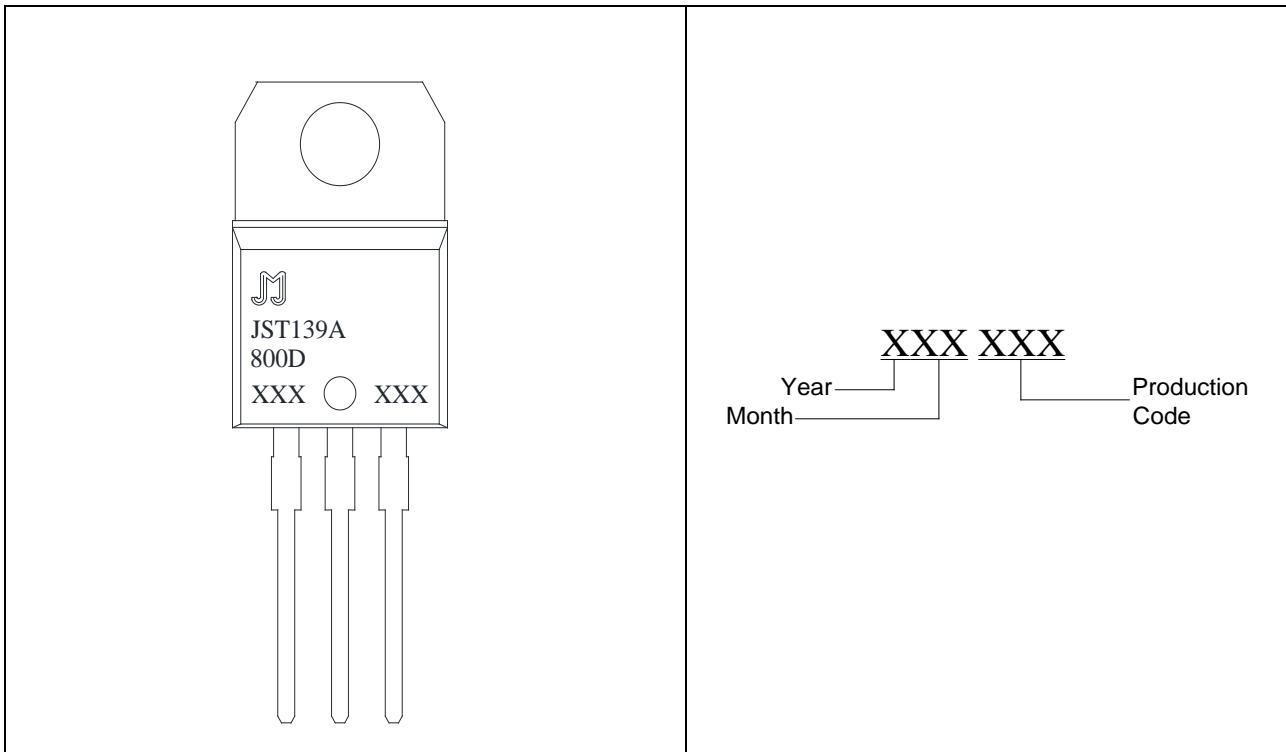
| Symbol           | Parameter   |                       | Value(MAX.) | Unit |
|------------------|---|-----------------------|-------------|------|
| V <sub>TM</sub>  | I <sub>TM</sub> =20A t <sub>p</sub> =380μs                        | T <sub>j</sub> =25°C  | 1.5         | V    |
| V <sub>TO</sub>  | Threshold voltage   | T <sub>j</sub> =125°C | 0.75        | V    |
| R <sub>D</sub>   | Dynamic resistance  | T <sub>j</sub> =125°C | 27          | mΩ   |
| I <sub>DRM</sub> | V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub> | T <sub>j</sub> =25°C  | 5           | μA   |
| I <sub>RRM</sub> |   | T <sub>j</sub> =125°C | 0.5         | mA   |

**THERMAL RESISTANCES**

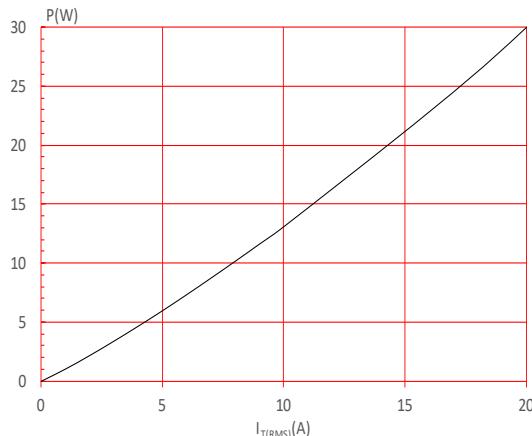
| Symbol               | Parameter                | Value | Unit |
|----------------------|--------------------------|-------|------|
| R <sub>th(j-c)</sub> | junction to case (AC)    | 2.3   | °C/W |
| R <sub>th(j-a)</sub> | junction to ambient (AC) | 60    | °C/W |

**ORDERING INFORMATION**

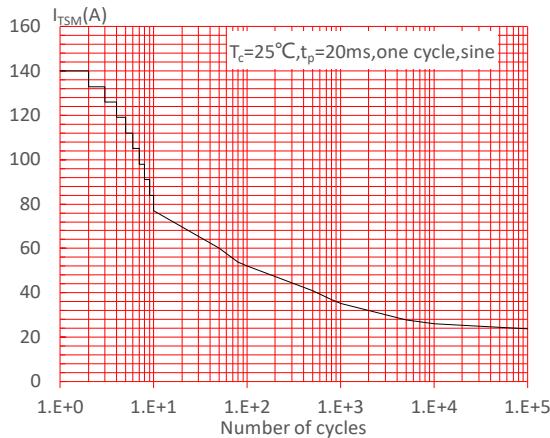
|                                   |           |             |                |  |  |
|-----------------------------------|-----------|-------------|----------------|--|--|
| <b>J</b>                          | <b>ST</b> | <b>139</b>  | <b>A</b>       | <b>-800</b>                                    | <b>D</b>   |
| JieJie Microelectronics Co., Ltd. |           |             |                |  |  |
|                                   | Triacs    |             |                |  |  |
|                                   |           | IT(RMS):16A |                |  |  |
|                                   |           |             | A:TO-220A(Ins) |  |  |
|                                   |           |             |                | 800:V <sub>DRM</sub> / V <sub>RRM</sub> ≥ 800V |  |
|                                   |           |             |                |  | D:IGT <sub>1-3</sub> ≤ 5mA I <sub>GTR</sub> ≤ 10mA |

**MARKING**

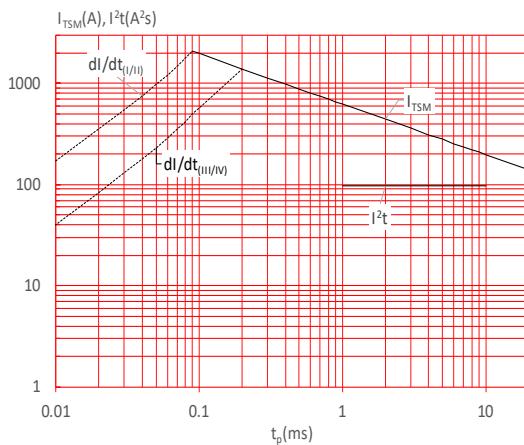
**FIG.1** Maximum power dissipation versus RMS on-state current



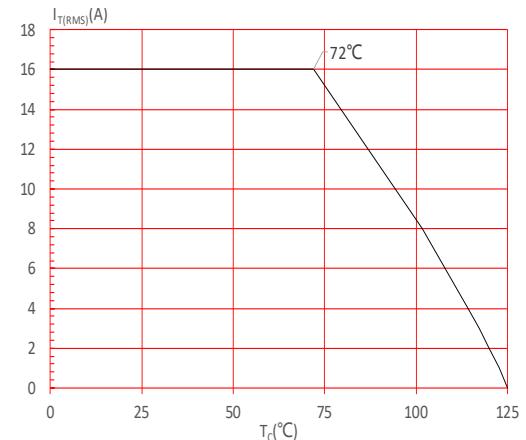
**FIG.3:** Surge peak on-state current versus number of cycles



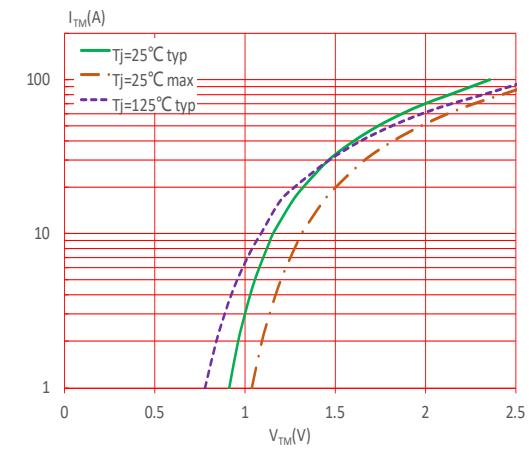
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$   
( I - II :  $dl/dt < 50\text{A}/\mu\text{s}$ ; III - IV :  $dl/dt < 20\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

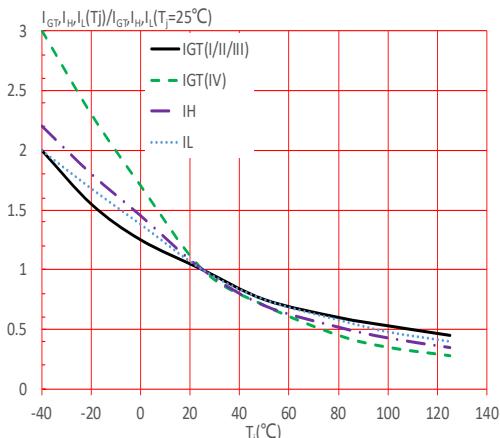
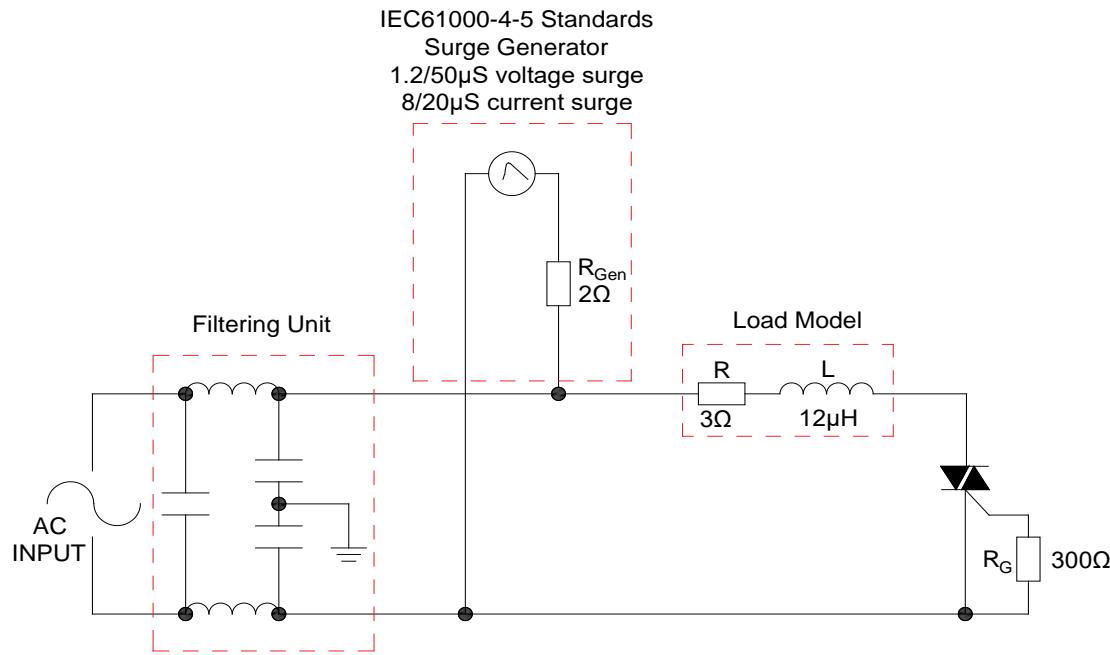


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

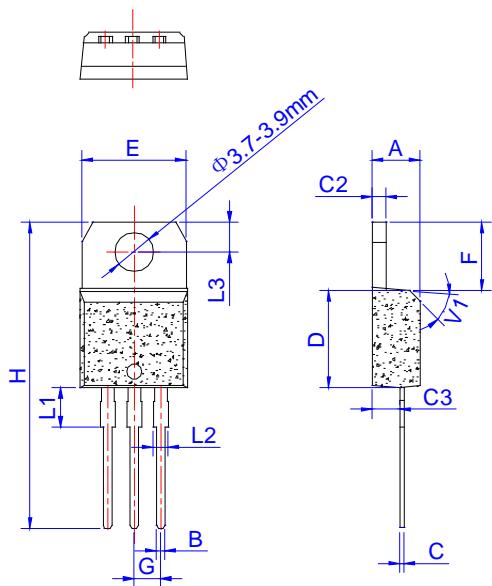
## ORDERING INFORMATION

| Order code   | Voltage<br>$V_{DRM}/V_{RRM}$ (V) | IGT(mA)      |    | Package      | Base qty.<br>(pcs) | Delivery mode |
|--------------|----------------------------------|--------------|----|--------------|--------------------|---------------|
|              |                                  | I - II - III | IV |              |                    |               |
| JST139A-800D | 800                              | 5            | 10 | TO-220A(Ins) | 50                 | Tube          |

## Document Revision History

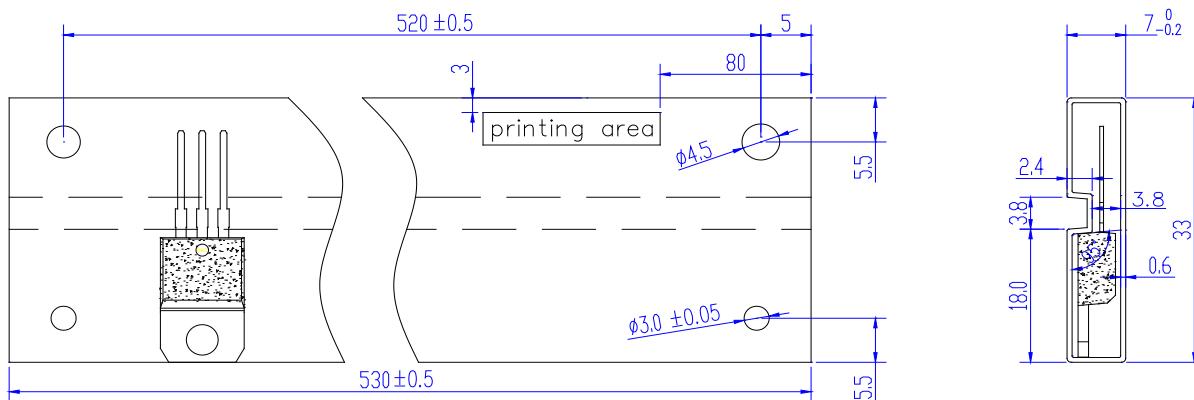
| Date         | Revision | Changes      |
|--------------|----------|--------------|
| Apr.14, 2023 | A.1.0    | Last updated |

## PACKAGE MECHANICAL DATA



| Ref. | Dimensions  |      |      |        |      |       |
|------|-------------|------|------|--------|------|-------|
|      | Millimeters |      |      | Inches |      |       |
|      | Min.        | Typ. | Max. | Min.   | Typ. | Max.  |
| A    | 4.40        |      | 4.60 | 0.173  |      | 0.181 |
| B    | 0.61        |      | 0.88 | 0.024  |      | 0.035 |
| C    | 0.46        |      | 0.70 | 0.018  |      | 0.028 |
| C2   | 1.21        |      | 1.32 | 0.048  |      | 0.052 |
| C3   | 2.40        |      | 2.72 | 0.094  |      | 0.107 |
| D    | 8.60        |      | 9.70 | 0.339  |      | 0.382 |
| E    | 9.80        |      | 10.4 | 0.386  |      | 0.409 |
| F    | 6.25        |      | 6.85 | 0.246  |      | 0.270 |
| G    | 2.40        |      | 2.70 | 0.094  |      | 0.106 |
| H    | 28.0        |      | 29.8 | 1.102  |      | 1.173 |
| L1   | 3.45        |      | 4.05 | 0.136  |      | 0.159 |
| L2   | 1.14        |      | 1.70 | 0.045  |      | 0.067 |
| L3   | 2.65        |      | 2.95 | 0.104  |      | 0.116 |
| V1   |             | 45°  |      |        | 45°  |       |

## DELIVERY MODE



| PACKAGE | OUTLINE | TUBE<br>(PCS) | INNER BOX<br>(PCS) | PER CARTON |
|---------|---------|---------------|--------------------|------------|
| TO-220A | TUBE    | 50            | 1,000              | 5,000      |

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